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DERWENT EPO; JPO; DERWENT EPO; JPO; DERWENT USPAT 1748 self adj (aligned or aligning or aligns or align) adj (contact or contacts) 67 (self adj (aligned or aligning or aligns or align) adj (contact or contacts) with (interdielectric or	_				
- 2 ((H01L\$4 and semiconductor) and (self adj aligned adj contact)) and (stopping adj layer) - 1748 self adj (aligned or aligning or aligns or align) adj (contact or contacts) - 67 (self adj (aligned or aligning or aligns or align) adj (contact or contacts)) and ((dry adj etch\$3) with (interdielectric or		1 523	(Fig. 1247 and semiconductor) and (sem adj anymed adj contact)		2003/03/03 02.17
contact)) and (stopping adj layer) self adj (aligned or aligning or aligns or align) adj (contact or contacts) 67 (self adj (aligned or aligning or aligns or align) adj (contact or contacts)) and ((dry adj etch\$3) with (interdielectric or			(/H041 64 and comice advictor) and (4516 54) alternal 54)		2002/05/05 00:40
- 1748 self adj (aligned or aligning or aligns or align) adj (contact or contacts) - 67 (self adj (aligned or aligning or aligns or align) adj (contact or contacts)) and ((dry adj etch\$3) with (interdielectric or	-	2			2003/05/05 02:18
contacts) - 67 (self adj (aligned or aligning or aligns or align) adj (contact or contacts)) and ((dry adj etch\$3) with (interdielectric or		4=45			0000/05/05 55 55
- 67 (self adj (aligned or aligning or aligns or align) adj (contact or contacts)) and ((dry adj etch\$3) with (interdielectric or	-	1748		USPAT	2003/05/05 02:26
contacts)) and ((dry adj etch\$3) with (interdielectric or				1	
	-	67		USPAT	2003/05/05 02:42
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-	0	planarizing with (gate adj upper adj dielectric)	USPAT	2003/05/05 02:44
-	0	planarize with (gate adj upper adj dielectric)	USPAT	2003/05/05 02:48
-	0	planar\$5 with (gate adj upper adj dielectric)	USPAT	2003/05/05 02:48
} -	1	gate adj upper adj dielectric	USPAT	2003/05/05 02:44
-	33	planarizing with (gate adj dielectric)	USPAT	2003/05/05 02:45
-	8	planarize with (gate adj dielectric)	USPAT	2003/05/05 02:48
] -	157	planar\$5 with (gate adj dielectric)	USPAT	2003/05/05 02:48
-	120	(planar\$5 with (gate adj dielectric)) not ((planarize with (gate	USPAT	2003/05/05 02:48
ļ		adj dielectric)) or (planarizing with (gate adj dielectric)))		(
-	8	(("6313018") or ("6287957") or ("6165901") or ("6204161") or	USPAT	2003/05/05 03:42
		("6507064") or ("6468859") or ("6380042") or ("6081016")).PN.		